

IN THE SPECIFICATION

Please substitute the following paragraph, page 3, line 14, which is marked up showing changes made, as follows:

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Q1 -- Figure 1 illustrates implantation depth of nitrogen ions utilizing a conventional plasma technique. A silicon dioxide layer 100 having a thickness of approximately 20 Å is formed on a silicon substrate 102. Nitrogen ions are implanted into the silicon dioxide layer 100 and also into the silicon 102 directly below the silicon dioxide layer 100. The nitrogen in the silicon 102 below the silicon dioxide layer 100 contaminates the silicon 102 resulting in a smaller current that flows through the silicon 102. [Too shallow of a nitridation] Nitridation that is too shallow can cause undesirable interfacial interactions and less optimal average dielectric constant. --

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